

ABSTRACT OF THE DISCLOSURE

The magneto-resistance effect element includes: a first ferromagnetic layer serving as a magnetization
5 fixed layer; a magnetization free layer including a second ferromagnetic layer provided on one side of the first ferromagnetic layer, a third ferromagnetic layer which is formed on an opposite side of the second ferromagnetic layer from the first ferromagnetic layer
10 and has a film face having an area larger than that of the second ferromagnetic layer and whose magnetization direction is changeable by an external magnetic field, and an intermediate layer which is provided between the second ferromagnetic layer and the third ferromagnetic
15 layer and which transmits a change of magnetization direction of the third ferromagnetic layer to the second ferromagnetic layer; and a tunnel barrier layer provided between the first ferromagnetic layer and the second ferromagnetic layer.

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